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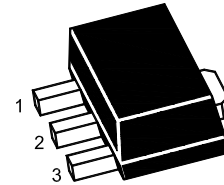
福 靈 有 限 公 司

FLAT P, 3/F., EVEREST INDUSTRIAL CENTRE, 396 KWUN TONG ROAD,
KWUN TONG, KOWLOON, HONG KONG.

TEL: 852-2790 0314 FAX: 852-2790 0206

ST 2SB1132U

PNP SILICON EPITAXIAL MEDIUM POWER TRANSISTOR



1.Base 2.Collector 3.Emitter
SOT-89 Plastic Package

Absolute Maximum Ratings (T_a = 25 °C)

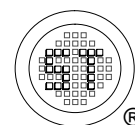
Parameter	Symbol	Value	Unit
Collector Base Voltage	-V _{CBO}	40	V
Collector Emitter Voltage	-V _{CEO}	32	V
Emitter Base Voltage	-V _{EBO}	5	V
Collector Current - DC	-I _C	1	A
Collector Current - Pulse ¹⁾	-I _{CP}	2	A
Total Power Dissipation	P _{tot}	0.5 2 ²⁾	W
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _S	- 55 to + 150	°C

¹⁾ Single pulse, PW = 100 ms.

²⁾ When mounted on a 40 X 40 X 0.7 mm ceramic board.

Characteristics at T_a = 25 °C

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at -V _{CE} = 3 V, -I _C = 100 mA Current Gain Group	P	82	-	180	-
	Q	120	-	270	-
	R	180	-	390	-
Collector Base Breakdown Voltage at -I _C = 50 μA	-V _{(BR)CBO}	40	-	-	V
Collector Emitter Breakdown Voltage at -I _C = 1 mA	-V _{(BR)CEO}	32	-	-	V
Emitter Base Breakdown Voltage at -I _E = 50 μA	-V _{(BR)EBO}	5	-	-	V
Collector Cutoff Current at -V _{CB} = 20 V	-I _{CBO}	-	-	0.5	μA
Emitter Cutoff Current at -V _{EB} = 4 V	-I _{EBO}	-	-	0.5	μA
Collector Emitter Saturation Voltage at -I _C = 500 mA, -I _B = 50 mA	-V _{CE(sat)}	-	-	0.5	V
Transition Frequency at I _E = 50 mA, -V _{CE} = 5 V, f = 30 MHz	f _T	-	150	-	MHz
Output Capacitance at -V _{CB} = 10 V, f = 1 MHz	C _{ob}	-	-	30	pF



Dated : 30/05/2006



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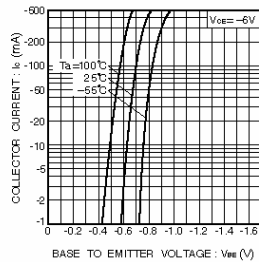


Fig.1 Grounded emitter propagation characteristics

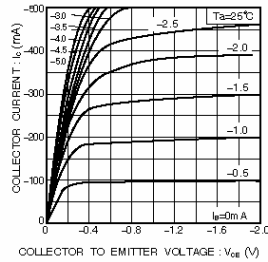


Fig.2 Grounded emitter output characteristics

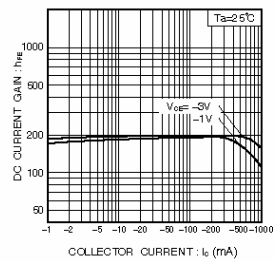


Fig.3 DC current gain vs. collector current(I)

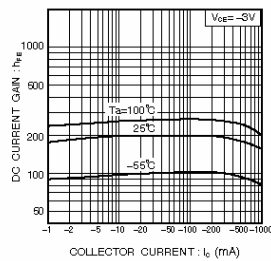


Fig.4 DC current gain vs. collector current(I)

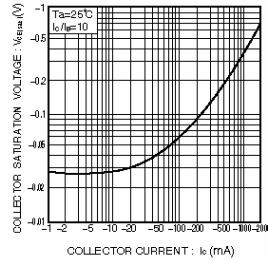


Fig.5 Collector-emitter saturation voltage vs. collector current

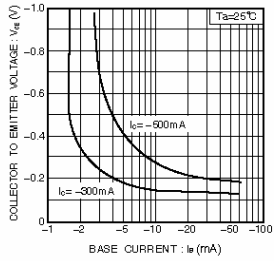


Fig.6 Collector-emitter saturation voltage vs. base current

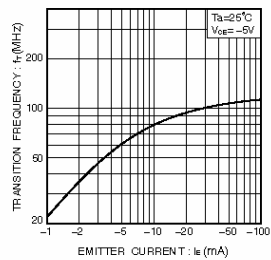


Fig.7 Gain bandwidth product vs. emitter current

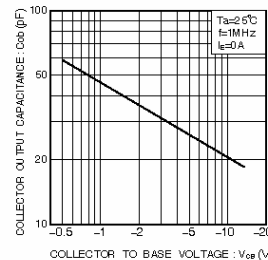


Fig.8 Collector output capacitance vs. collector-base voltage

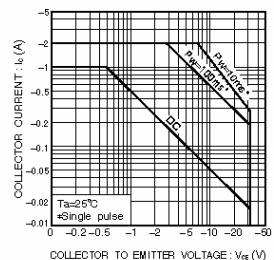


Fig.9 Safe operation area

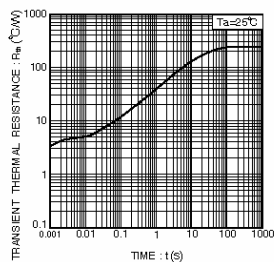
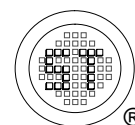


Fig.10 Transient thermal resistance





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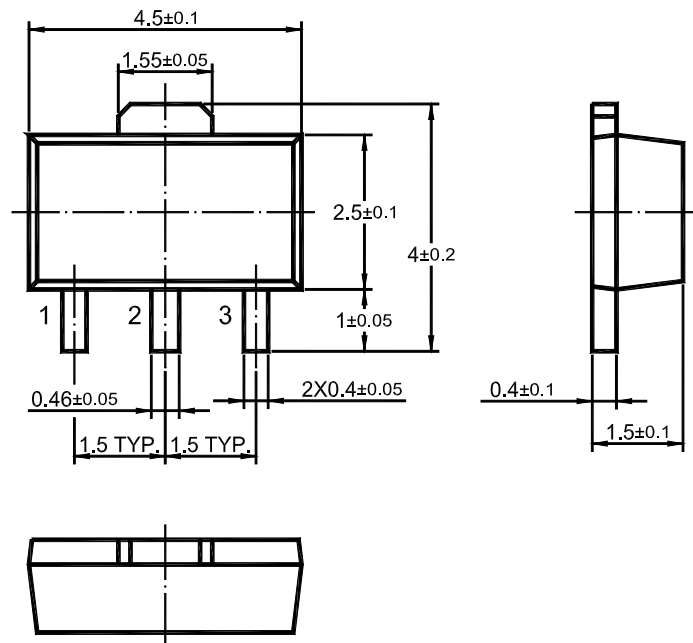
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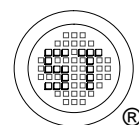
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SOT-89 PACKAGE OUTLINE



Dimensions in mm



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